



Features:

- Drives two N-channel MOSFETs or IGBTs in a half bridge configuration
- Floating high-side driver in bootstrap operation to 600V/290mA source/600mA sink output current capability
- Outputs tolerant to negative transients
- Internal logic and deadtime (100ns) to protect MOSFETs
- Logic input (HIN and LIN) 3.3V capability
- Schmitt triggered logic inputs with internal pull down
- Undervoltage lockout for high and low side drivers
- Extended temperature range: -40°C to +125°C

Description

The SES2304M is a high voltage, high speed gate driver capable of driving N-channel MOSFETs and IGBTs in a half-bridge configuration. SSC Semi's high voltage process enables the SES2304M's high side to switch to 600V in a bootstrap operation.

The SES2304M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction. An internal deadtime of 100ns protects high-voltage MOSFETs from shoot-through.

The SES2304M is offered in 8-pin PDIP and SOIC narrow package and operates over an extended -40°C to +125°C temperature range.

Typical Application

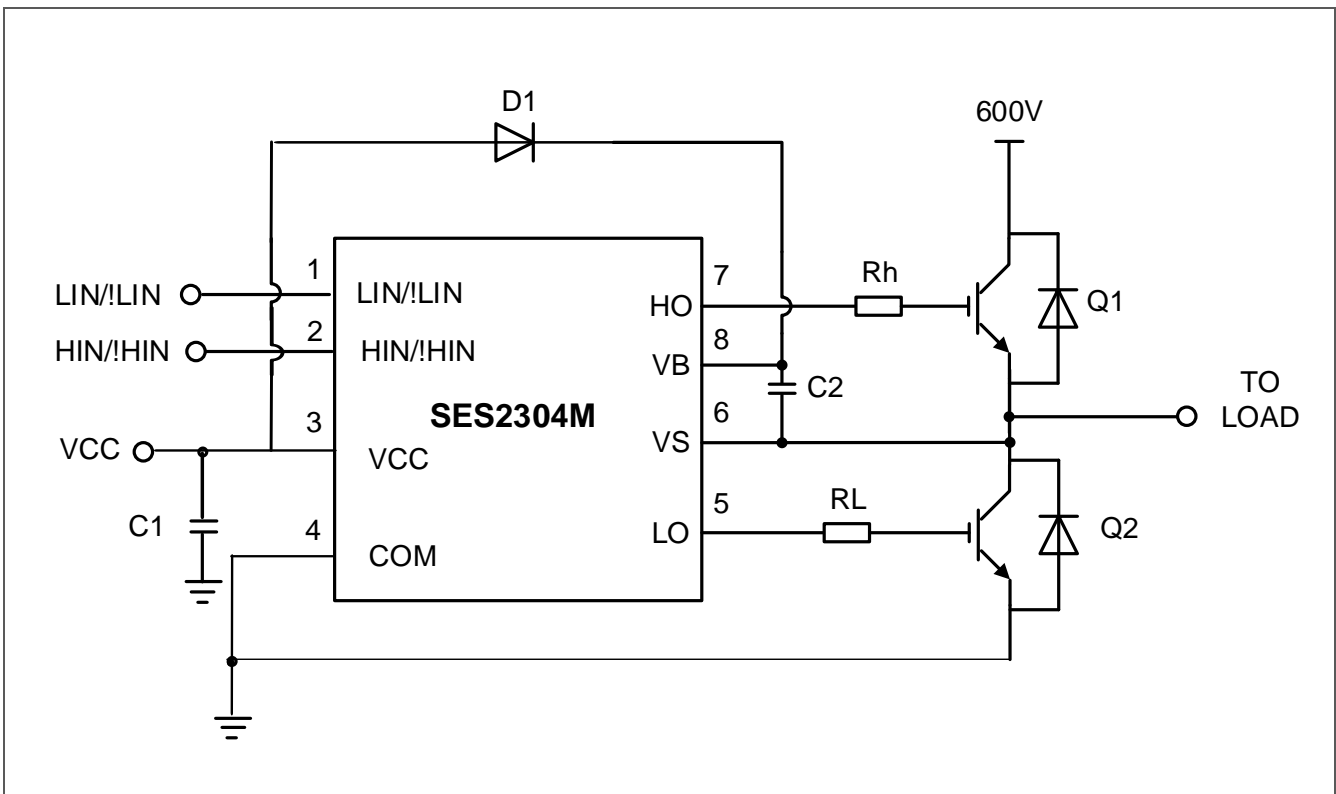
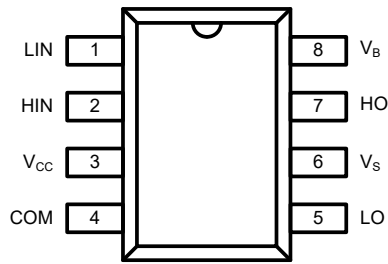


Figure 1: Typical applications of the SES2304M

Table 1: Recommended parameters for typical application devices

Device	D1	C1	C2	Rh / RL	Q1 / Q2
TYP	MUR180	4.7uF / 25v	0.1uF / 63V	10Ω	SGD02N60

Pin Diagrams



Top View: SOIC-8, PDIP-8

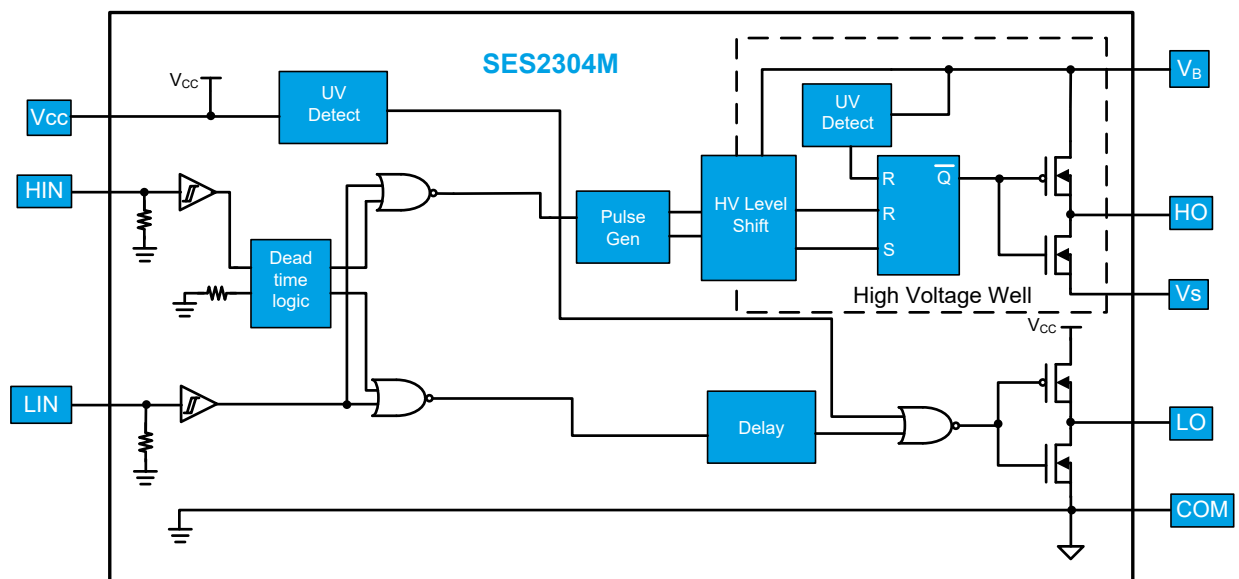
SES2304M

Figure 2: Pipe pin distribution of the SES2304M

Table 2: Function description of SES2304M

PIN NAME	PIN DESCRIPTION
HIN	Logic input for high-side gate driver output, in phase with HO
LIN	Logic input for low side gate driver output, in phase with LO
COM	Low-side and logic return
LO	Low-side gate drive output
V _{CC}	Low-side and logic fixed supply
V _S	High-side floating supply return
HO	High-side gate drive output
V _B	High-side floating supply

Functional Block Diagram



Absolute Maximum Ratings (NOTE1)

V_B - High side floating supply voltage.....-0.3V to +624V
 V_S - High side floating supply offset voltage..... V_B -24V to V_B +0.3V
 V_{HO} - High side floating output voltage..... V_S -0.3V to V_B +0.3V
 dV_S/dt - Offset supply voltage transient.....50 V/ns

V_{CC} - Low side and logic fixed supply voltage.....-0.3V to +24V
 V_{LO} - Low side output voltage.....-0.3V to V_{CC} +0.3V
 V_{IN} - Logic input voltage (HIN and LIN)..... V_{SS} - 0.3V to V_{CC} +0.3V

P_D - Package power dissipation at $T_A \leq 25^\circ\text{C}$
 SOIC-8.....1.25W
 PDIP-8.....1.6W

NOTE1 Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

PDIP-8 Thermal Resistance (NOTE2)

θ_{JC}15 °C/W
 θ_{JA}45 °C/W

SOIC-8(N) Thermal Resistance (NOTE2)

θ_{JC}25 °C/W
 θ_{JA}55 °C/W

T_J - Junction operating temperature+150 °C
 T_L - Lead temperature (soldering, 10s) +300 °C
 T_{stg} - Storage temperature range-55 °C to +150 °C

NOTE2 When mounted on a standard JEDEC 2-layer FR-4 board.

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
V_B	High side floating supply absolute voltage	$V_S + 10$	$V_S + 22$	V
V_S	High side floating supply offset voltage	(NOTE 3)	600	V
V_{HO}	High side floating output voltage	V_S	V_B	V
V_{CC}	Low side and logic fixed supply voltage	10	22	V
V_{LO}	Low side output voltage	0	V_{CC}	V
V_{IN}	Logic input voltage	0	5	V
T_A	Ambient temperature	-40	125	°C

DC Electrical Characteristics (NOTE4)

$V_{BIAS} (V_{CC}, V_{BS}) = 15V$ and $T_A = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V_{IH}	Logic "1" input voltage	$V_{CC} = 10V$ to $22V$ NOTE 5	2.3			V
V_{IL}	Logic "0" input voltage					
V_{OH}	High level output voltage, $V_{BIAS} - V_O$	$I_O = 2mA$		0.05	0.2	
V_{OL}	Low level output voltage, V_O	$I_O = 2mA$		0.02	0.1	
I_{LK}	Offset supply leakage current	$V_B = V_S = 600V$			50	μA
I_{BSQ}	Quiescent V_{BS} supply current	$V_{IN} = 0V$ or $5V$	20	60	150	
I_{CCQ}	Quiescent V_{CC} supply current	$V_{IN} = 0V$ or $5V$	50	260	400	μA
I_{IN+}	Logic "1" input bias current	$V_{IN} = 5V$		5	40	μA
I_{IN-}	Logic "0" input bias current	$V_{IN} = 0V$		1.0	5.0	
V_{BSUV+}	V_{BS} supply under-voltage positive going threshold		7.7	8.7	9.7	V
V_{BSUV-}	V_{BS} supply under-voltage negative going threshold		7.0	8.0	9.0	
V_{CCUV+}	V_{CC} supply under-voltage positive going threshold		7.7	8.7	9.7	
V_{CCUV-}	V_{CC} supply under-voltage negative going threshold		7.0	8.0	9.0	
I_{O+}	Output high short circuit pulsed current	$V_O = 0V$, $PW \leq 10\ \mu s$	60	290		mA
I_{O-}	Output low short circuit pulsed current	$V_O = 15V$, $PW \leq 10\ \mu s$	130	600		

NOTE4 The V_{IH} , V_{IL} , I_{IN} parameters are referenced to COM and are applicable to the two logic input pins: HIN and LIN. The V_O and I_O parameters are referenced to COM and are applicable to the respective output pins: HO and LO.

NOTES For optimal operation, it is recommended that the input pulse (to HIN and LIN) should have an amplitude of 2.3V minimum with a pulse width of 200ns minimum.

AC Electrical Characteristics

$V_{BIAS} (V_{CC}, V_{BS}) = 15V$ and $C_L = 1000\text{ pF}$, and $T_A = 25\text{ }^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t_{ON}	Turn-on propagation delay	$V_S = 0V$		95	210	ns
t_{OFF}	Turn-off propagation delay	$V_S = 0V$ or $600V$		100	210	
t_{DMON}	Delay matching HS & LS turn on/off				50	
t_r	Turn-on rise time			70	120	
t_f	Turn-off fall time			35	60	
t_{DT}	Deadtime: $t_{DT\ LO-HO}$ & $t_{DT\ HO-LO}$		80	100	190	

Timing Waveforms

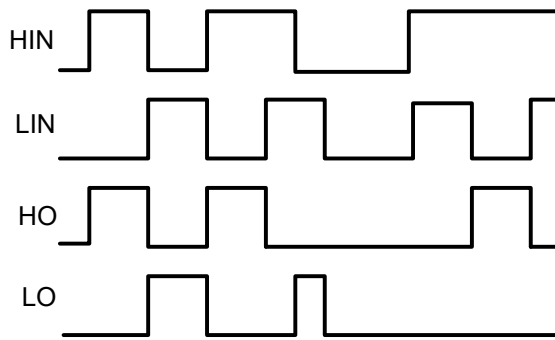


Figure 3. Input / Output Timing Diagram

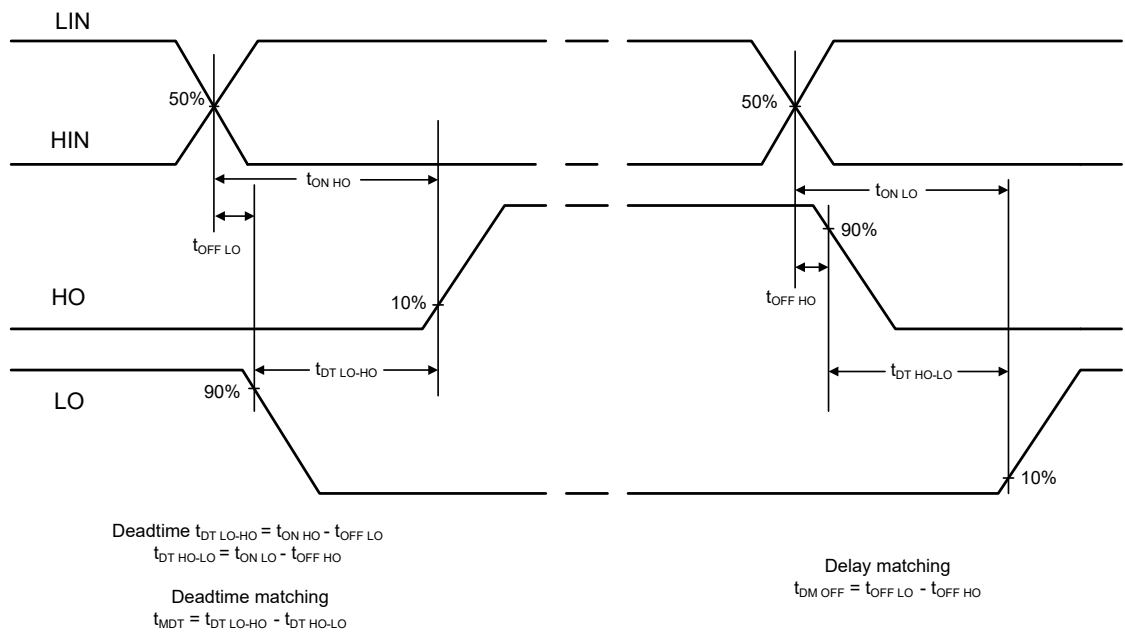
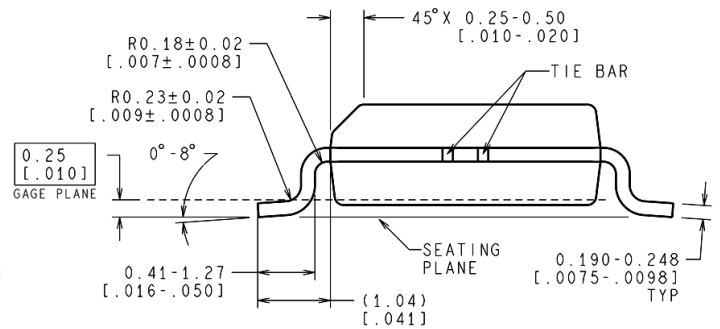
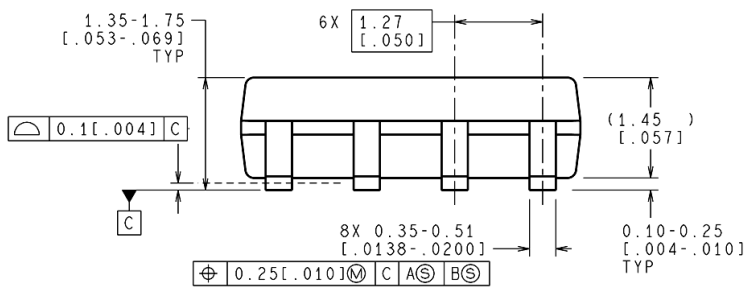
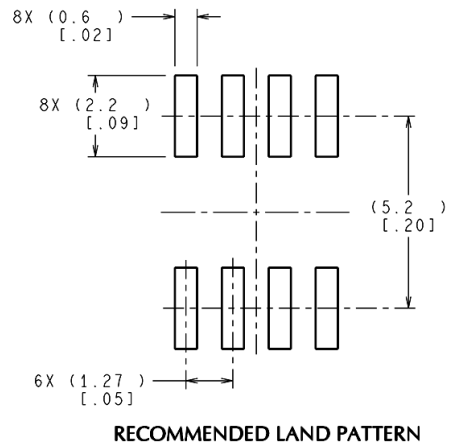
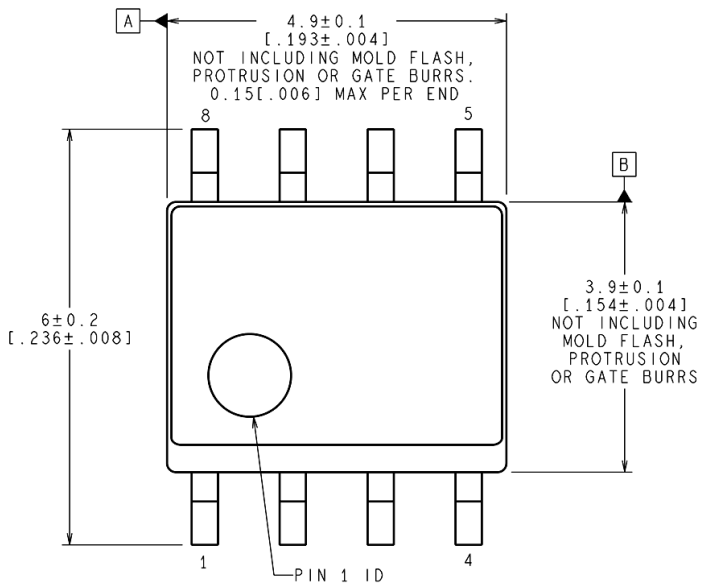


Figure 4. Switching Time Waveform Definition

Package Dimensions (SOIC-8N)

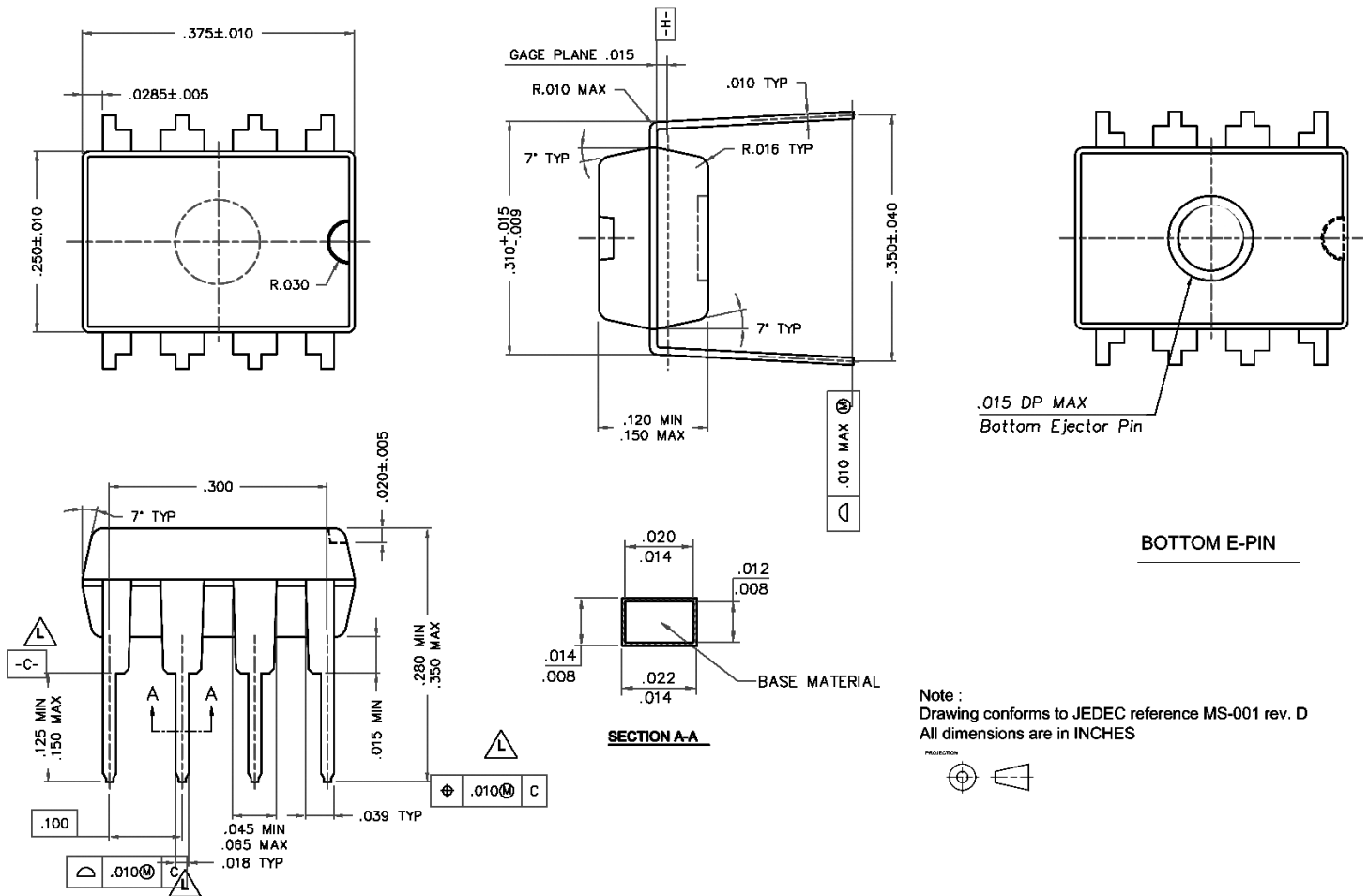


NOTES: UNLESS OTHERWISE SPECIFIED

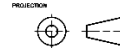
1. REFERENCE JEDEC REGISTRATION MS-012, VARIATION AA.

CONTROLLING DIMENSION IS MILLIMETER
VALUES IN [] ARE INCHES
DIMENSIONS IN () FOR REFERENCE ONLY

Package Dimensions (PDIP-8)



Note :
 Drawing conforms to JEDEC reference MS-001 rev. D
 All dimensions are in INCHES



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Revision History

Revision	Change	Page	Author	Date
a / 1st version			Allen	2019.02
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